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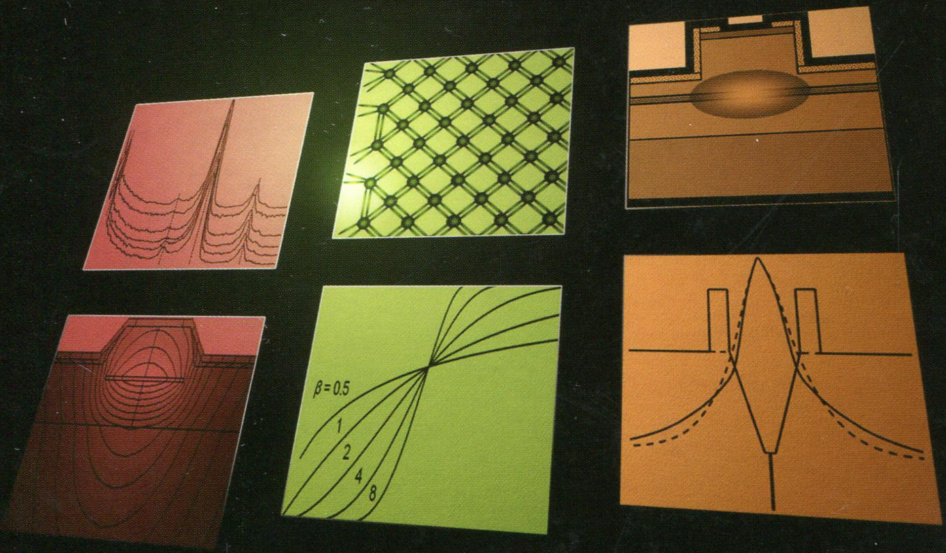

A Practical Approach to High Power and Single Mode Devices

Peter W. Epperlein

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